

Data Sheet January 2002

## 4A, 200V Ultrafast Diodes

The RURD420S is an ultrafast diode with soft recovery characteristics ( $t_{rr}$  < 30ns). It has low forward voltage drop and has ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. It's low stored charge and ultrafast soft recovery minimize ringing and electrical noise in many power switching circuits, reducing power loss in the switching transistors.

Formerly developmental type TA49034.

## **Ordering Information**

PART NUMBER	PACKAGE	BRAND
RURD420S	TO-252	RUR420

NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-252 variant in tape and reel, i.e., RURD420S9A.

# FeaturesUltrafast w

Ultrafast with Soft Recovery	<30ns
Operating Temperature	175 <sup>0</sup> C
Reverse Voltage	200V

- · Avalanche Energy Rated
- Planar Construction

## **Applications**

- · Switching Power Supplies
- · Power Switching Circuits
- General Purpose

# **Packaging**

**JEDEC STYLE TO-252** 



# Symbol



#### **Absolute Maximum Ratings** T<sub>C</sub> = 25°C, Unless Otherwise Specified

	RURD420S	UNITS
Peak Repetitive Reverse Voltage	200	V
Working Peak Reverse Voltage	200	V
DC Blocking Voltage V <sub>R</sub>	200	V
Average Rectified Forward Current	4	Α
$(T_C = 159^{\circ}C)$		
Repetitive Peak Surge Current	8	Α
(Square Wave, 20kHz)		
Nonrepetitive Peak Surge Current	40	Α
(Halfwave, 1 Phase, 60Hz)		
Maximum Power Dissipation	30	W
Avalanche Energy (See Figures 9 and 10)	10	mJ
Operating and Storage Temperature	-65 to 175	°C
Maximum Lead Temperature for Soldering		
(Leads at 0.063 in. (1.6mm) from case for 10s)	300	°C
Package Body for 10s, see Tech Brief 334	260	°С

# **Electrical Specifications** $T_C = 25^{\circ}C$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V <sub>F</sub>	I <sub>F</sub> = 4A	-	-	1.0	V
	$I_F = 4A, T_C = 150^{\circ}C$	-	-	0.83	V

**Electrical Specifications**  $T_C = 25^{\circ}C$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
I <sub>R</sub>	V <sub>R</sub> = 200V	-	-	100	μΑ
	V <sub>R</sub> = 200V, T <sub>C</sub> = 150°C	-	-	500	μΑ
t <sub>rr</sub>	I <sub>F</sub> = 1A, dI <sub>F</sub> /dt = 100A/μs	-	-	30	ns
	I <sub>F</sub> = 4A, dI <sub>F</sub> /dt = 100A/μs	-	-	35	ns
t <sub>a</sub>	$I_F = 4A$ , $dI_F/dt = 100A/\mu s$	-	11	-	ns
t <sub>b</sub>	$I_F = 4A$ , $dI_F/dt = 100A/\mu s$	-	9	-	ns
Q <sub>RR</sub>	$I_F = 4A$ , $dI_F/dt = 100A/\mu s$	-	12	-	nC
СЛ	V <sub>R</sub> = 10V, I <sub>F</sub> = 0A	-	15	-	pF
$R_{ heta JC}$		-	-	5	°C/W

#### **DEFINITIONS**

 $V_F$  = Instantaneous forward voltage (pw = 300 $\mu$ s, D = 2%).

I<sub>R</sub> = Instantaneous reverse current.

 $t_{\mbox{\scriptsize rr}}$  = Reverse recovery time (See Figure 8), summation of  $t_{\mbox{\scriptsize a}}$  +  $t_{\mbox{\scriptsize b}}$ .

 $t_a$  = Time to reach peak reverse current (See Figure 8).

t<sub>b</sub> = Time from peak I<sub>RM</sub> to projected zero crossing of I<sub>RM</sub> based on a straight line from peak I<sub>RM</sub> through 25% of I<sub>RM</sub> (See Figure 8).

Q<sub>RR</sub> = Reverse recovery charge.

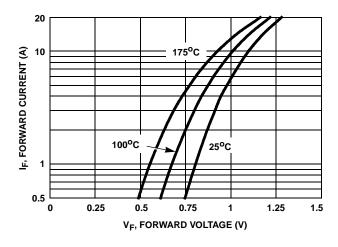
 $C_J$  = Junction capacitance.

 $R_{\theta JC}$  = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

# **Typical Performance Curves**





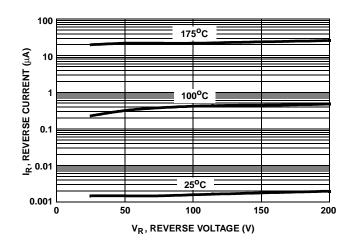


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

#### Typical Performance Curves (Continued)

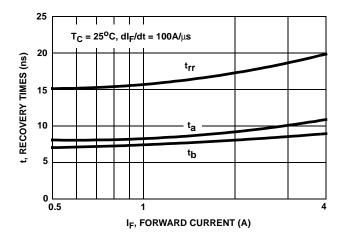


FIGURE 3.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

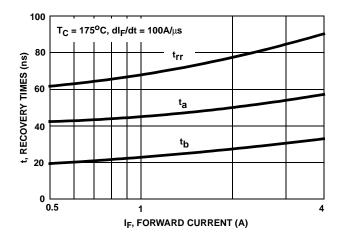


FIGURE 5.  $t_{rr}$ ,  $t_a$  and  $t_b$  curves vs forward current

Test Circuits and Waveforms

# V<sub>GE</sub> AMPLITUDE AND R<sub>G</sub> CONTROL di<sub>F</sub>/dt t<sub>1 AND</sub> t<sub>2</sub> CONTROL I<sub>F</sub> DUT CURRENT SENSE V<sub>GE</sub> V<sub>DD</sub>

FIGURE 7.  $t_{rr}$  TEST CIRCUIT

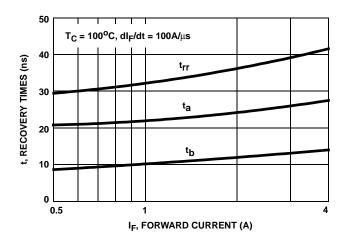


FIGURE 4.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

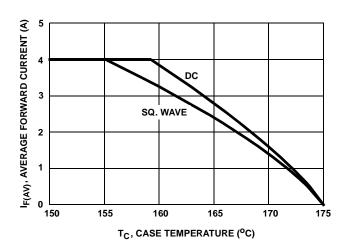


FIGURE 6. CURRENT DERATING CURVE

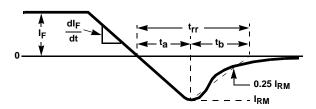


FIGURE 8.  $t_{rr}$  WAVEFORMS AND DEFINITIONS

# Test Circuits and Waveforms (Continued)

I = 1A L = 20mH  $R < 0.1\Omega$   $E_{AVL} = 1/2LI^{2} [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$   $Q_{1} = IGBT (BV_{CES} > DUT V_{R(AVL)})$  L CURRENT SENSE  $V_{DD}$   $U_{DUT}$   $V_{DD}$ 

FIGURE 9. AVALANCHE ENERGY TEST CIRCUIT

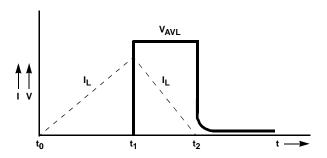


FIGURE 10. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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CROSSVOLT™	FRFET™	MicroPak™	$QS^{TM}$	SyncFET™
DOME™	GlobalOptoisolator™	MICROWIRE™	QT Optoelectronics™	TinyLogic <sup>®</sup>
EcoSPARK™	GTO™ .	MSX <sup>TM</sup>	Quiet Series™	TINYOPTO™
E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	RapidConfigure™	TruTranslation™
EnSigna™	I <sup>2</sup> C <sup>TM</sup>	$OCX^{TM}$	RapidConnect™	UHC™
FACT™	ImpliedDisconnect™	OCXPro™	SILENT SWITCHER®	UltraFET®
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#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
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